

PRELIMINARY AMENDMENT

Serial Number: 09/382,442

Filing Date: August 25, 1999

Title: METHOD FOR REDUCING SINGLE BIT DATA LOSS IN A MEMORY CIRCUIT

Page 2

Dkt: 303.522US1

9. (Amended) The method of claim 7 and further comprising forming a film comprising Hydrogen isotope within the gate region of the memory circuit in order to reduce single bit data loss.

26. (Amended) A method of forming a non-volatile electrically alterable semiconductor memory cell with reduced, random, single bit data loss in a memory circuit comprising:
providing a silicon substrate;
fabricating a field oxide region and a channel region over or within the silicon substrate;
growing an oxide over the channel region in an atmosphere
enriched in Hydrogen isotope;
fabricating at least one gate member; and
passivating the memory cell comprising single bit data in an atmosphere that comprises Hydrogen isotope thereby reducing single bit data loss.

35. (Amended) A method for passivating a non-volatile, electrically alterable semiconductor memory cell, thereby reducing random, single bit data loss in a memory circuit, comprising:
providing a non-volatile, electrically alterable semiconductor memory cell comprising single bit data; and
exposing the memory cell to an atmosphere that comprises Hydrogen isotope thereby reducing single bit data loss.

37. (Amended) A method for overlaying source and drain regions of a non-volatile, electrically alterable semiconductor memory cell with a thermal oxide layer thereby reducing random, single bit data loss in a memory circuit, comprising:
providing a silicon substrate and providing a memory cell comprising single bit data;
defining source and drain regions in the silicon substrate; and
growing the thermal oxide layer over the source and drain regions in an atmosphere that comprises Hydrogen isotope thereby reducing single bit data loss in the memory cell.